

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	19	(polycrystalline adj resistor) and program\$5	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/11 14:11
L2	74598	resistor and program\$5	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/11 14:11
L3	1231	2 and polycrystalline	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/11 14:11
L4	1086	3 and current	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/11 14:11
L5	4	3 and (current adj stress)	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/11 14:13
L6	1013	4 and silicon	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/11 14:14
L7	111	6 and (control adj voltage)	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/11 14:20
L8	1013	6 and current	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/11 14:20
L9	242	8 and stress	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/11 14:20
L10	0	9 and (control adj voltage adj level)	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/11 14:21
L11	68	9 and (threshold adj voltage)	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/11 14:40
L12	167	9 and memory	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/11 14:40

L13	135	12 and data	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/11 14:41
L14	72	13 and MOS	USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/06/11 14:41